

No.2754

2 S C 4 4 0 1

NPN Epitaxial Planar Silicon Transistor

VHF/UHF Mixer, Local Oscillator, Low-Voltage Amp Applications

Applications

. VHF/UHF MIX/OSC, low-voltage high-frequency amplifiers

Features

· Low-voltage operation : $f_T = 3.0 GHz$ typ ($V_{CE} = 3V$)

: MAG=11dB typ ($V_{CE}=3V,I_{C}=3mA$)

 $: NF = 3.0 dB \text{ typ } (V_{CE} = 3V, I_{C} = 3mA)$

· Very small-sized package permitting 2SC4401-applied sets to be made smaller and slimmer

Maximum Ratings at Ta = 25°C		unit
or to Base Voltage V _{CBO}	25	V
or to Emitter Voltage V _{CEO}	15	V
r to Base Voltage V _{EBO}	3	V
or Current I _C	30	mΑ
or Dissipation P _C	150	mW
n Temperature Tj	150	$^{\circ}\mathrm{C}$
Temperature Tstg	55 to +150	°C
or to Emitter Voltage VCEO r to Base Voltage VEBO or Current IC or Dissipation PC on Temperature Tj	15 3 30 150 150	V W mA mW

Electrical Characteristics at Ta=	25°C		min	typ	max	unit
Collector Cutoff Current	I_{CBO}	$V_{CB}=15V,I_{E}=0$			1.0	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 2V, I_C = 0$			1.0	μA
DC Current Gain	h_{FE}	$V_{CE}=3V,I_{C}=3mA$	※40		%200	_
Gain-Bandwidth Product	$\mathbf{f_T}$	$V_{CE}=3V,I_{C}=3mA$		3.0		GHz
Output Capacitance	c_{ob}	$V_{CB} = 3V, f = 1MHz$		0.7	1.3	\mathbf{pF}
Reverse Transfer Capacitance	c _{re}	$V_{CB} = 3V, f = 1MHz$		0.65		рF
Forward Transfer Gain	S2le ²	$V_{CE} = 3V, I_{C} = 3mA, f = 0.9GHz$		7		ďΒ
Maximum Available Power Gain	MAG	$V_{CE}=3V,I_{C}=3mA,f=0.9GHz$		11		dB
Noise Figure	NF	$V_{CE} = 3V, I_{C} = 3mA, f = 0.9GHz$		3.0	5.0	dB
-		See specified Test Circuit.				

* The 2SC4401 is classified by 3mA hFE as follows:

4	10	2	80	60	3	120	100	4	200	

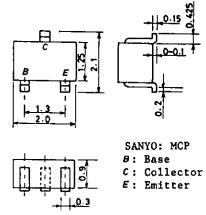
(Note)

Marking: OT hee rank: 2,3,4

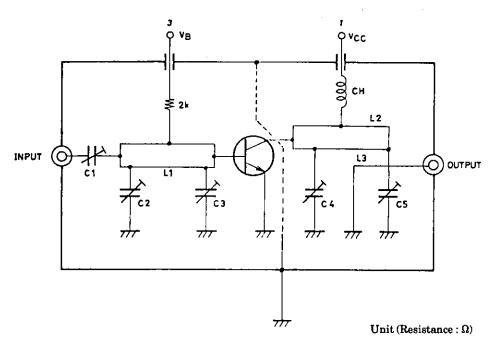
•For CP package version, use the 2SC4364.

Package Dimensions 2059

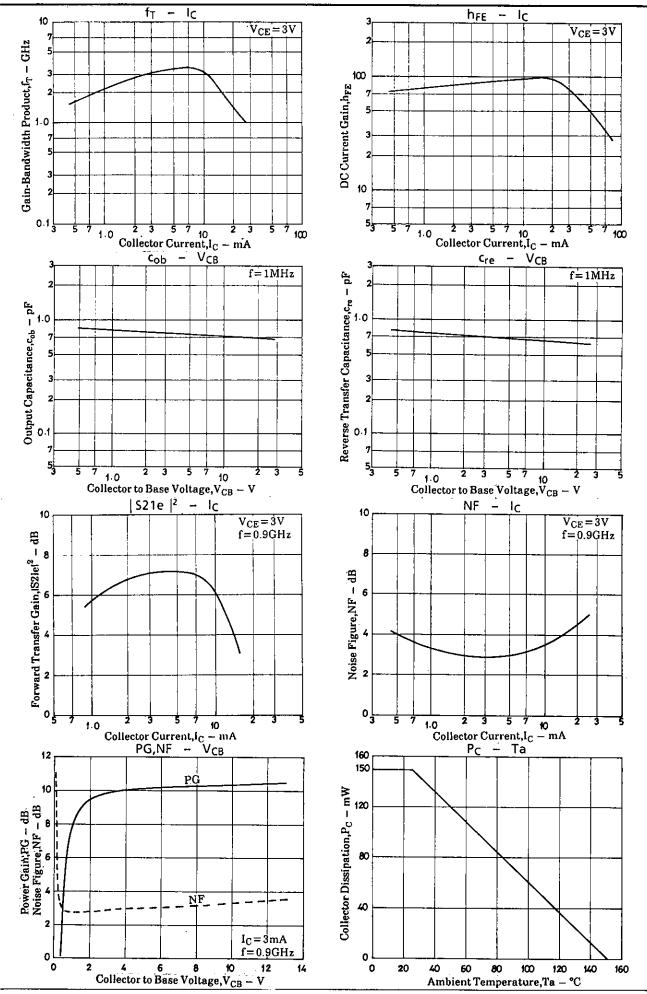
(unit: mm)



NF Test Circuit



	900MHz
C 1	~5 p F
C 2	~1 O p F
С3	~10pF
C 4	~10pF
С 5	~10pF
L 1	W ≑1 .5mm, l ≑2 5mm
	strip line
L 2	W≑4mm, 1 ÷ 25mm
	strip line
L3	0.5φ, 1 ÷40mm
СН	2t + bead core



\$11e: V_{CE} = 3V

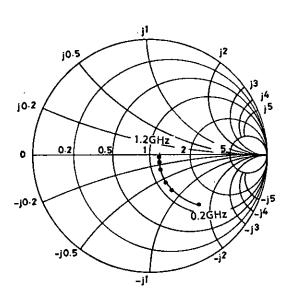
 $I_C = 3mA$

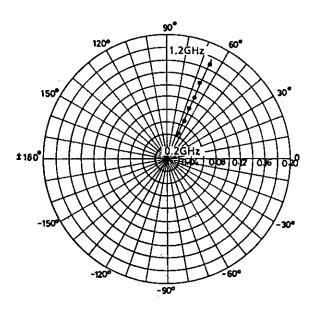
f = 0.2GHz step

\$12e: V_{CE} = 3V

 $I_C = 3mA$

f = 0.2GHz step



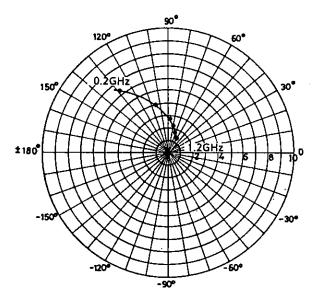


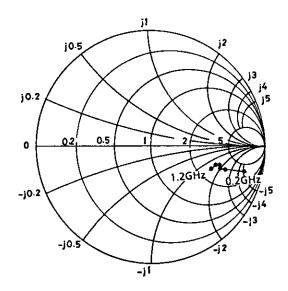
S21e: V_{CE} = 3V

 $I_C = 3mA$

f = 0.2GHz step

S22e: $V_{CE} = 3V$ $I_C = 3mA$ f = 0.2GHz step





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